

Amendments to the Claims:

Claims 1-15 have been amended herein. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application. No new matter has been added.

Listing of Claims:

1. (Currently amended) A semiconductor device assembly, comprising:
a carrier substrate comprising a substantially planar structure with a surface including at least one first contact area thereon, proximate at least one opening formed through ~~said the~~ carrier substrate; and
a solder mask comprising at least one opening through which ~~said the~~ at least one opening and ~~said the~~ at least one first contact area of ~~said the~~ carrier substrate are exposed;
wherein the carrier substrate comprises an insulative material.

2. (Currently amended) The semiconductor device assembly of claim 1, further comprising:
at least one semiconductor die secured to another surface of ~~said the~~ carrier substrate opposite ~~said the~~ surface thereof, at least one bond pad of ~~said the~~ at least one semiconductor die being exposed through ~~said the~~ at least one opening of ~~said the~~ solder mask and ~~said the~~ at least one opening of ~~said the~~ carrier substrate.

3. (Currently amended) The semiconductor device assembly of claim 2, further comprising:
at least one intermediate conductive element extending between ~~said the~~ at least one bond pad and ~~said the~~ at least one first contact area.

4. (Currently amended) The semiconductor device assembly of claim 3, wherein a thickness of ~~said-the~~ solder mask exceeds a height ~~said-of the~~ at least one intermediate conductive element that protrudes above ~~said-the~~ surface of ~~said-the~~ carrier substrate.

5. (Currently amended) The semiconductor device assembly of claim 3, further comprising:
a quantity of encapsulant material within ~~said-the~~ at least one opening of ~~said-the~~ carrier substrate and ~~said-the~~ at least one opening of ~~said-the~~ solder mask.

6. (Currently amended) The semiconductor device assembly of claim 5, wherein an upper surface of ~~said-the~~ quantity of encapsulant material is substantially level with an outer surface of ~~said-the~~ solder mask.

7. (Currently amended) The semiconductor device assembly of claim 5, wherein a distance between an uppermost portion of ~~said-the~~ at least one intermediate conductive element and an outer surface of ~~said-the~~ solder mask is at least about 25 μm .

8. (Currently amended) The semiconductor device assembly of claim 7, wherein ~~said-the~~ at least one intermediate conductive element comprises a bond wire and a thickness of ~~said-the~~ solder mask is equal to the sum of a distance of a portion of a loop of ~~said-the~~ bond wire that protrudes above ~~said-the~~ surface of ~~said-the~~ carrier substrate and about 25 μm .

9. (Currently amended) The semiconductor device assembly of claim 1, wherein ~~said-the~~ carrier substrate includes at least one second contact area on ~~said-the~~ surface thereof and at least one conductive trace electrically connecting ~~said-the~~ at least one first contact area and ~~said-the~~ at least one second contact area.

10. (Currently amended) The semiconductor device assembly of claim 9, wherein ~~said the~~ at least one second contact area is at least partially exposed through an aperture of ~~said the~~ solder mask.

11. (Currently amended) The semiconductor device assembly of claim 10, further comprising:
at least one discrete conductive element protruding from ~~said the~~ at least one second contact area above ~~said the~~ solder mask.

12. (Currently amended) The semiconductor device assembly of claim 11, wherein at least half of a height of ~~said the~~ at least one discrete conductive element protrudes above an outer surface of ~~said the~~ solder mask.

13. (Currently amended) The semiconductor device assembly of claim 1, wherein ~~said the~~ solder mask comprises a material with a coefficient of thermal expansion substantially the same as a material of ~~said the~~ carrier substrate.

14. (Currently amended) The semiconductor device assembly of claim 1, wherein ~~said the~~ solder mask comprises a cured photoimageable material.

15. (Currently amended) The semiconductor device assembly of claim 1, wherein a thickness of ~~said the~~ solder mask is about 50 μm to about 100 μm .